

Hyperfast Rectifier, 2 A FRED Pt®

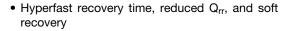




SMA (DO-214AC)

PRODUCT SUMMARY				
Package	SMA (DO-214AC)			
I _{F(AV)}	2 A			
V_{R}	200 V			
V _F at I _F	0.75 V			
t _{rr}	25 ns			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES





RoHS

COMPLIANT **HALOGEN**

FREE

- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- · Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		200	V
Average rectified forward current	I _{F(AV)}	T _{Sp} = 138 °C	2	۸
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C, 6 ms square pulse	50	A
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-	
Compared voltages may disade	V _F	I _F = 2 A	-	0.88	0.95	V
Forward voltage, per diode	٧F	I _F = 2 A, T _J = 125 °C	-	0.75	0.82	
Reverse leakage current, per diode	1	$V_R = V_R$ rated	-	-	2	
	I'R	$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	1	8	μA
Junction capacitance	C _T	V _R = 200 V	_	8	_	pF



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
			I _F = 1 A, dI _F /dt = 50 A/μs, V _R = 30 V		24	-	
Reverse recovery time		I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	25	1
neverse recovery time	Reverse recovery time t _{rr}	T _J = 25 °C		-	16	-	ns
		T _J = 125 °C		-	22	-	
Peak recovery current I _{RRM}	T _J = 25 °C	$I_F = 2 A,$ $dI_F/dt = 200 A/\mu s,$ $V_B = 160 V$	-	2	-	^	
	T _J = 125 °C		-	3	-	- A	
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	16	-	nC
	T _J = 125 °C		-	30	-	iiC	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to case	R_{thJC}	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	11	21	°C/W
Approximate weight				0.07		g
Approximate weight				0.002		oz.
Marking device		Case style SMA (DO-214AC)		21	1 2	

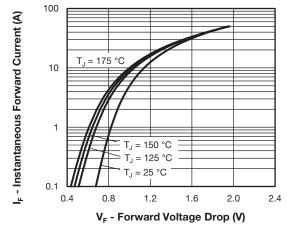


Fig. 1 - Typical Forward Voltage Drop Characteristics

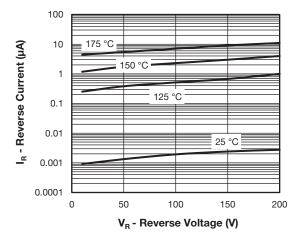


Fig. 2 - Typical Values of Reverse Current vs.
Reverse Voltage

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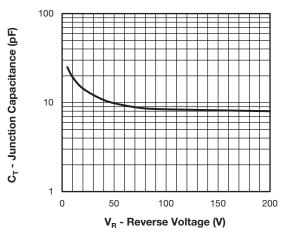


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

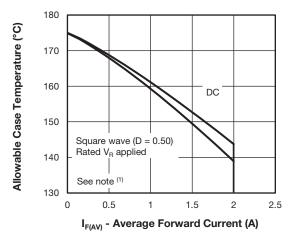


Fig. 4 - Maximum Allowable Case Temperature vs.
Average Forward Current

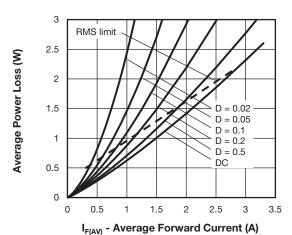


Fig. 5 - Forward Power Loss Characteristics

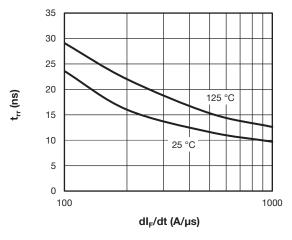


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

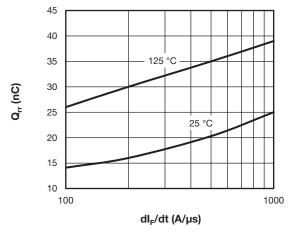
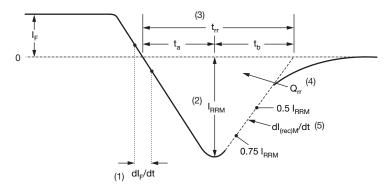


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5);} \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\rm Q_{rr}$ area under curve defined by $\rm t_{rr}$ and $\rm I_{RRM}$

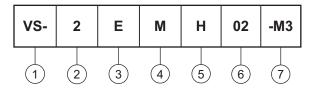
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current rating (2 = 2 A)
- 3 Circuit configuration:

E = single diode

4 - M = SMA package

5 - Process type,

H = hyperfast recovery

6 - Voltage code (02 = 200 V)

7 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-2EMH02-M3/5AT	7500	7500	13"diameter plastic tape and reel		

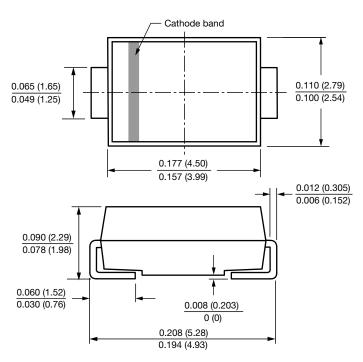
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95400		
Part marking information	www.vishay.com/doc?95472		
Packaging information	www.vishay.com/doc?95404		



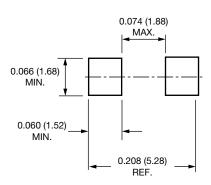
SMA

DIMENSIONS in inches (millimeters)

DO-214AC (SMA)



Mounting Pad Layout





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Vishay

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